Amendments to the Claims

1. (Currently amended) A wafer support tower for supporting wafers in parallel [[in]] spaced relationship along a vertical axis, comprising:

two silicon bases;

a plurality of silicon legs joined at opposite ends to said two bases; and

a plurality of teeth cut into said legs at an upwardly sloping angle of between 1° and 3° with respect to said vertical axis to support said wafers on upper sides of distal ends thereof.

2. (Original) The tower of Claim 1, wherein said silicon legs comprise virgin polysilicon.

3. (Original) The tower of Claim 2, wherein said virgin polysilicon has been annealed.

4. (Original) The tower of Claim 1, wherein support surfaces extending perpendicularly to said axis are formed in said distal ends to support said wafers.

5. (Original) The tower of Claim 4, wherein said support surfaces are polished.

6. (Original) The tower of Claim 4, wherein said support surfaces support said wafers at places located at between 69% and 72% of a radius of said wafers.

7. (Original) The tower of Claim 4, wherein said teeth have a generally wedge shape with said support surfaces being formed in a narrower side of said wedge shape.

8. (Original) The tower of Claim 1, wherein said teeth have a generally wedge shape with said distal ends being located in a narrower side of said wedge shape.

9. (Original) The tower of Claim 1, wherein said plurality of legs consists of either three or four of said legs.

10. (Original) A method of fabricating a silicon support tower, comprising the steps of:

in each of a plurality of silicon legs extending along a first axis, cutting a plurality of parallel slots to form teeth therebetween inclined at an angle of between 1° and 3° to a first side of said teeth with respect to a perpendicular to said first axis; and

joining opposite ends of said plurality of silicon legs to respective ones of two silicon bases to allow said teeth to support a plurality of wafers on said first sides thereof.

11. (Original) The method of claim 10, wherein said silicon legs comprise virgin polysilicon.

12. (Original) The method of claim 10, wherein said legs are annealed prior to said cutting step.

13. (Original) The method of claim 10, further comprising forming support surfaces extending perpendicularly to said first axis on said first sides of said teeth at distal ends thereof.

14. (New) A support tower for supporting wafers in parallel spaced relationship along a vertical axis, comprising:

two bases;

a plurality of legs joined at opposite ends to said two bases and disposable along said vertical axis;

a plurality of support teeth formed in said legs to have upper sloping surfaces sloping upwardly at a predetermined finite angle of no more than 3° with respect to said vertical axis; and

support surfaces extending perpendicularly to said vertical axis formed in said upper horizontal surfaces at distal ends of said support teeth to support said wafers thereon.

15. (New) The tower of Claim 14, wherein said bases and legs are formed of silicon members.

16. (New) The tower of Claim 15, wherein said legs are formed of virgin polysilicon members.

17. (New) The tower of Claim 14, wherein said legs are formed of quartz members.

18. (New) The tower of Claim 14, wherein said legs are formed of silicon carbide members.

19. (New) The tower of Claim 14, wherein said angle is at least 1°.

20. (New) The tower of Claim 19, wherein said bases and legs are formed of silicon members.

21. (New) The tower of Claim 14, wherein said support surfaces support said wafers at places located at between 69% and 72% of a radius of said wafers.

22. (New) The tower of Claim 14, wherein said teeth have generally wedge shapes with said distal ends being located in a narrower side of said wedge shapes.